

**AMENDMENTS TO THE CLAIMS:**

The following listing of claims will replace all prior versions and listings of claims in this divisional application.

**LISTING OF CLAIMS:**

Claims 1-5. (Cancelled)

Claim 6. (Currently Amended) A method for manufacturing a trench isolation on a silicon substrate, comprising:

forming a trench area for device isolation in the silicon substrate, wherein the trench has inner sidewalls;

forming an oxide layer on a surface of the silicon substrate that forms the inner sidewalls of the trench;

supplying healing elements to the silicon substrate to remove dangling bonds; and

filling the trench with a device isolation layer

~~The method for manufacturing a trench isolation on a silicon substrate as claimed in claim 1,~~ wherein supplying the healing elements comprises:

forming an ion implanting layer on the oxide layer;

implanting the healing elements in the ion implanting layer by an ion implantation; and

diffusing the ion implanted healing elements by means of a thermal annealing process.

7. The method for manufacturing a trench isolation on a silicon substrate as claimed in claim 6, wherein the ion implanting layer is a polysilicon layer.

Claims 8-31. (Cancelled)